



## TO-92 Plastic-Encapsulate Transistors

**2N5551** TRANSISTOR (NPN)

### FEATURES

- General Purpose Switching Application

### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

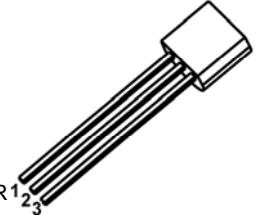
Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	0.6	A
$P_C$	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^\circ\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$

TO - 92

1. EMITTER

2. BASE

3. COLLECTOR



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=1\text{mA}, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=120\text{V}, I_E=0$			50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=1\text{mA}$	80			
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	80		300	
	$h_{FE(3)}$	$V_{CE}=5\text{V}, I_C=50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat) (1)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.15	V
	$V_{CE(sat) (2)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat) (1)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1	V
	$V_{BE(sat) (2)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			1	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			6	pF
Emitter input capacitance	$C_{ib}$	$V_{BE}=0.5\text{V}, I_C=0, f=1\text{MHz}$			20	pF
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100		300	MHz

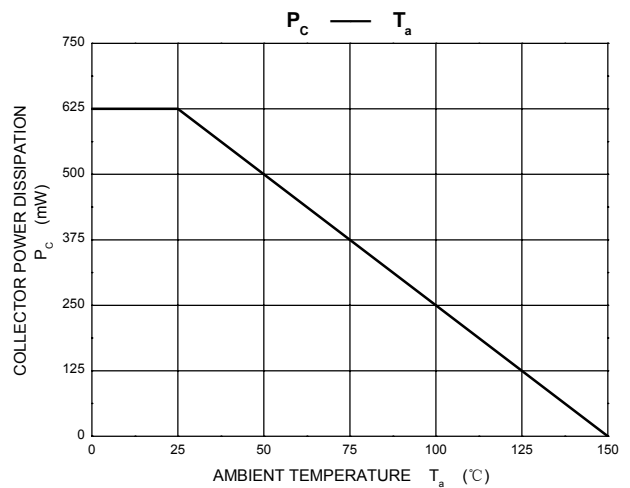
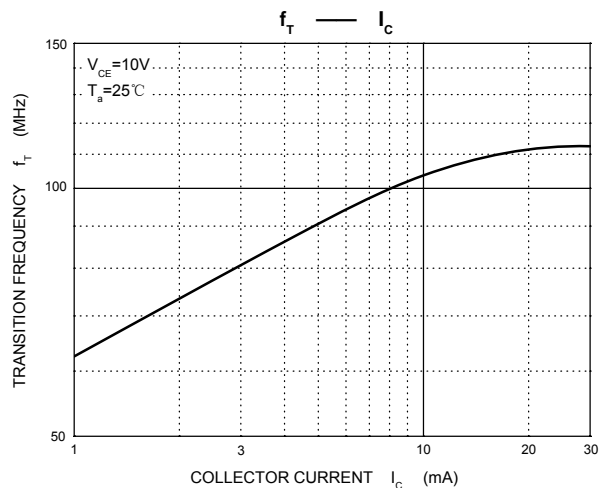
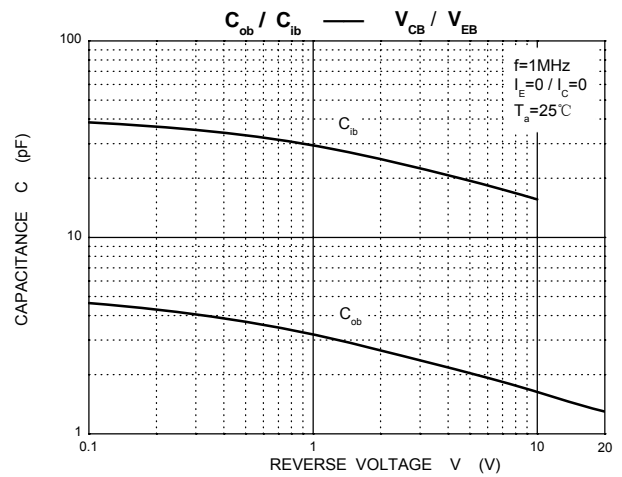
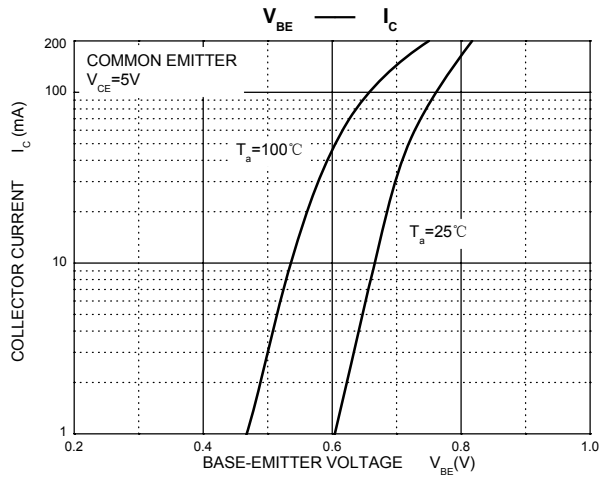
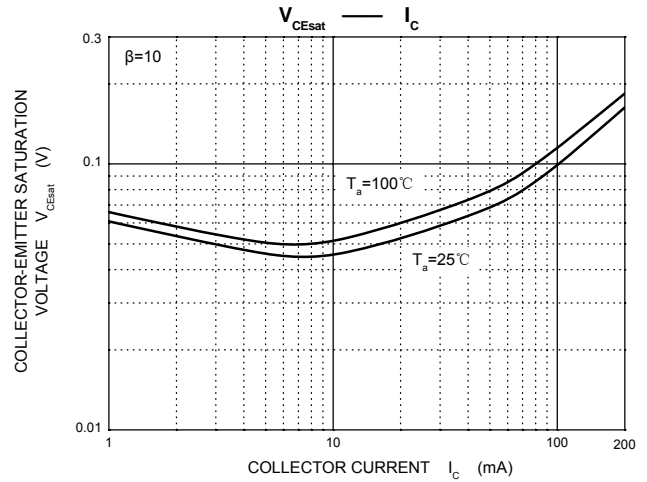
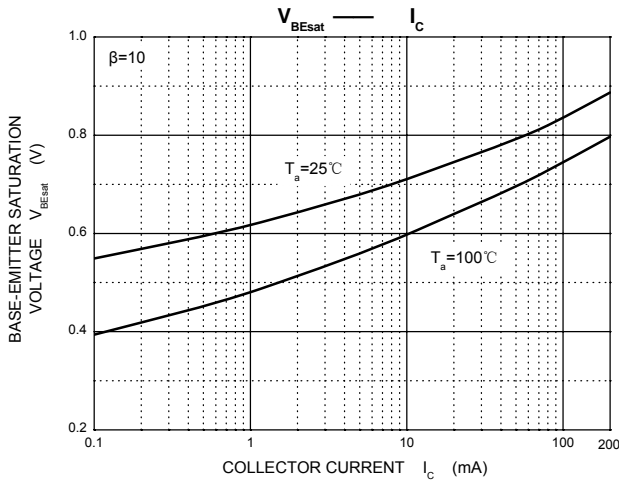
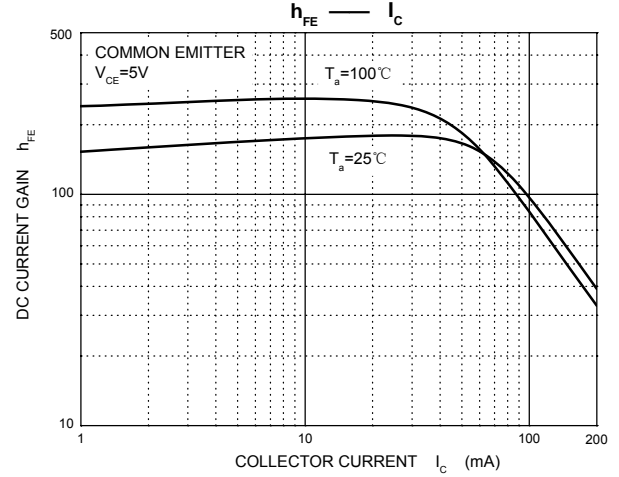
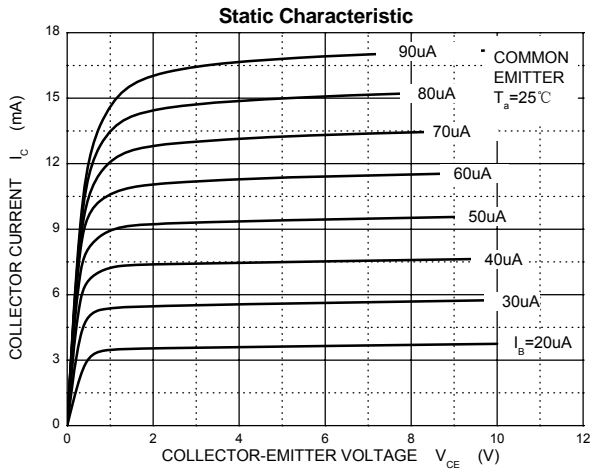
\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycles  $\leq 2.0\%$ .

### CLASSIFICATION OF $h_{FE(2)}$

RANK		A	B	C
RANGE	80-100	100-150	150-200	200-300

# Typical Characteristics

# 2N5551



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [Changjiang manufacturer](#):*

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)  
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)  
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-](#)  
[TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)  
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)  
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)